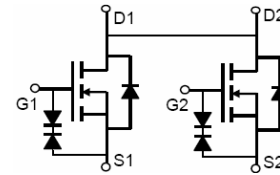


N-Channel Enhancement Mode Power MOSFET

Description

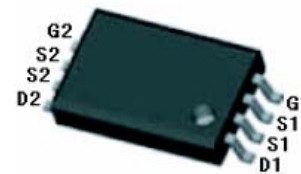
The FNK2012E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.



Schematic diagram

General Features

- $V_{DS} = 20V, I_D = 8A$
- $R_{DS(ON)} < 17m\Omega @ V_{GS}=2.5V$
- $R_{DS(ON)} < 13m\Omega @ V_{GS}=4.5V$
- ESD Rating: 2000V HBM
- High power and current handling capability
- Lead free product is acquired
- Surface mount package



TSSOP-8 top view

Application

- Uni-directional load switch
- Bi-directional load switch

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK2012E	FNK2012E	TSSOP-8	Ø330mm	12mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	8	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	62.5	$^\circ C/W$
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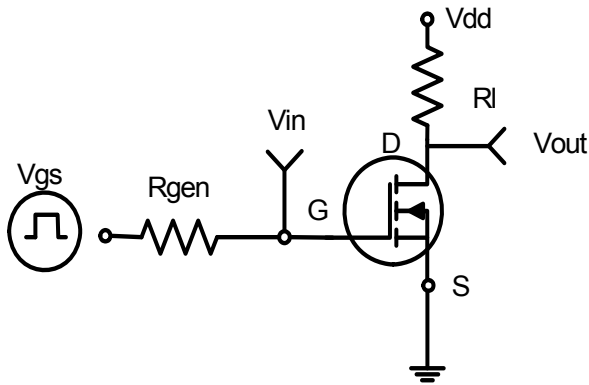
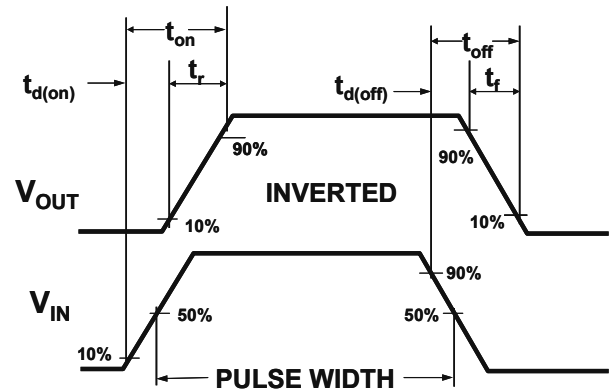
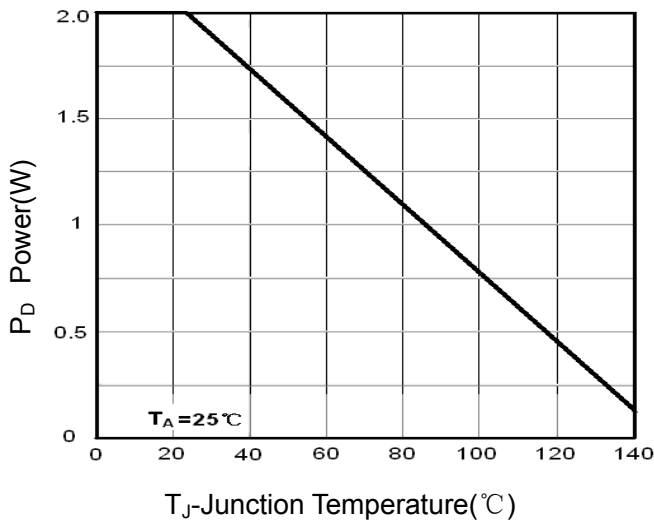
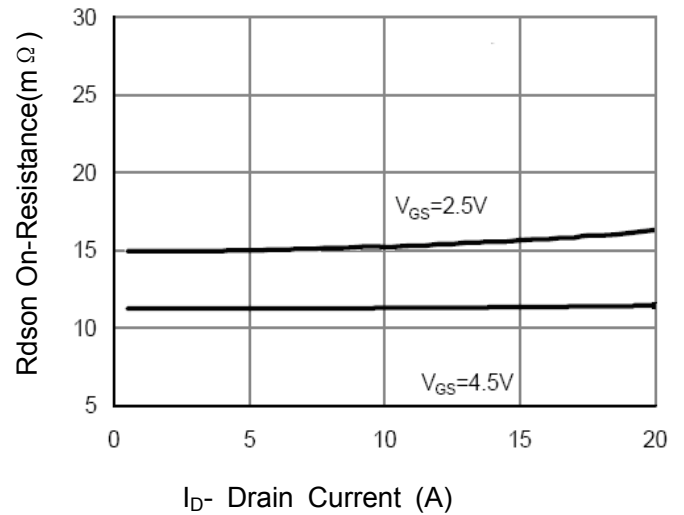
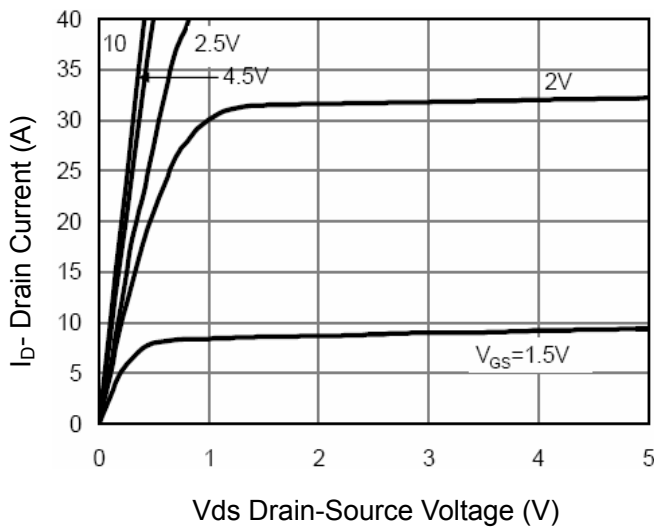
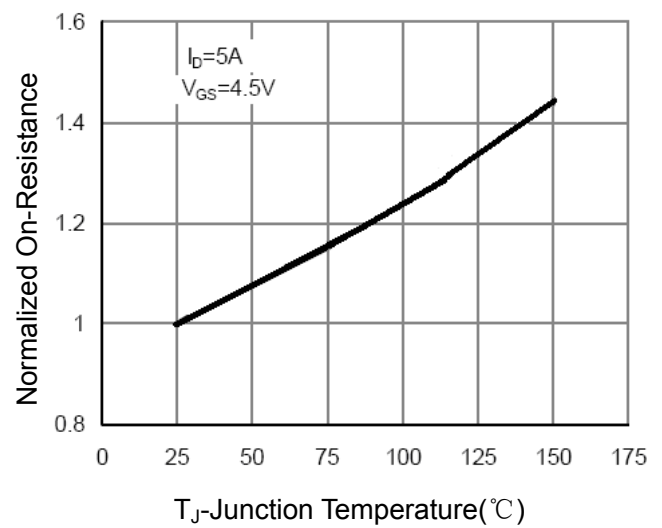
Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

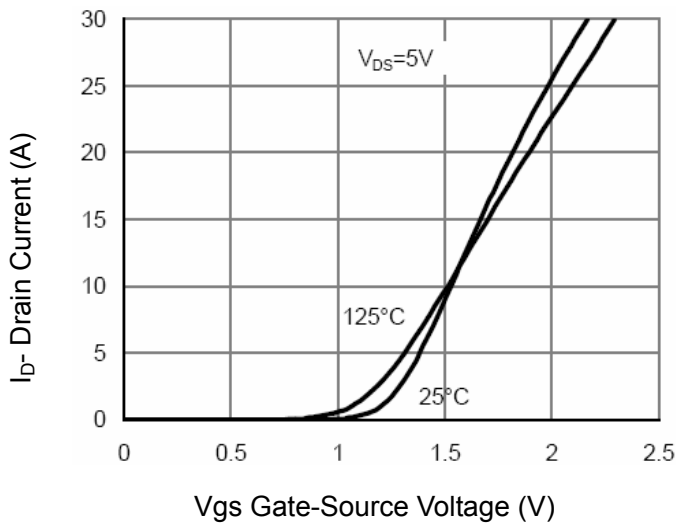
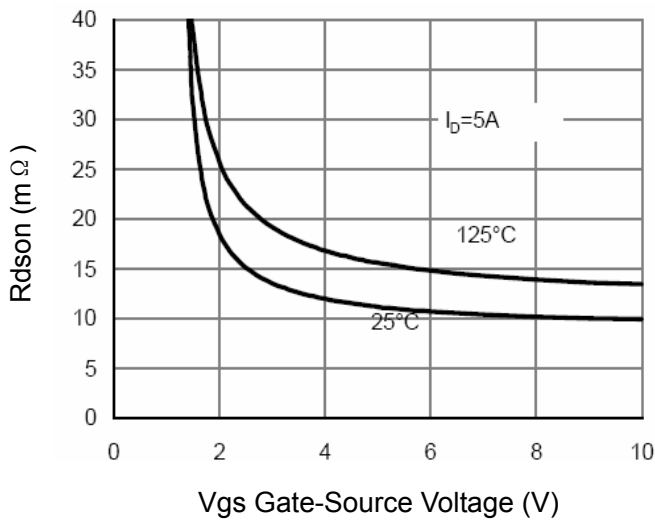
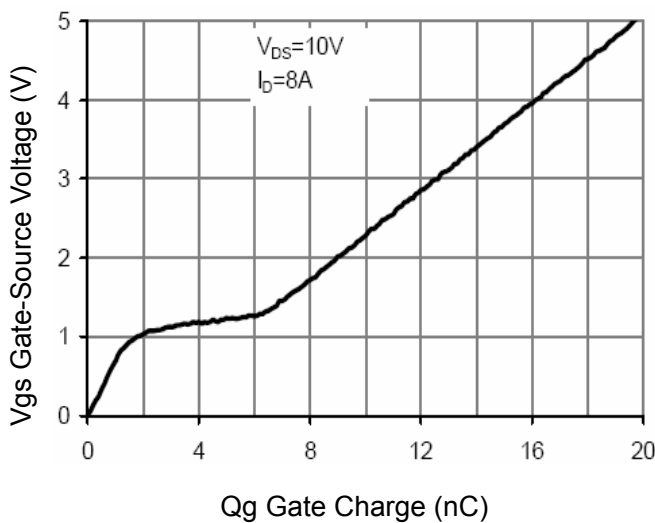
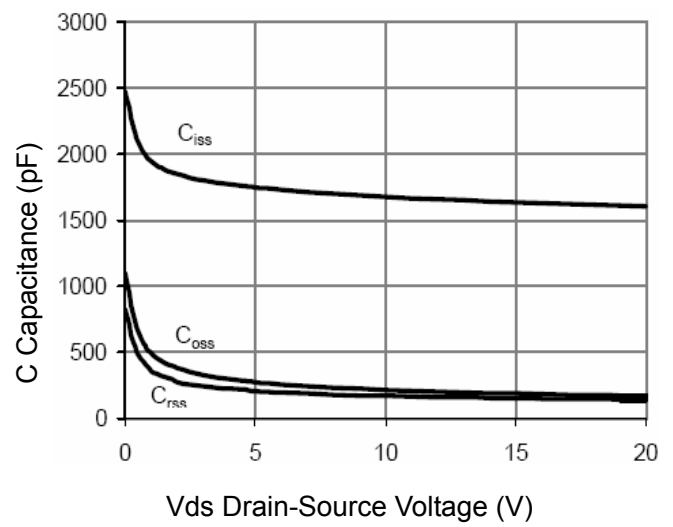
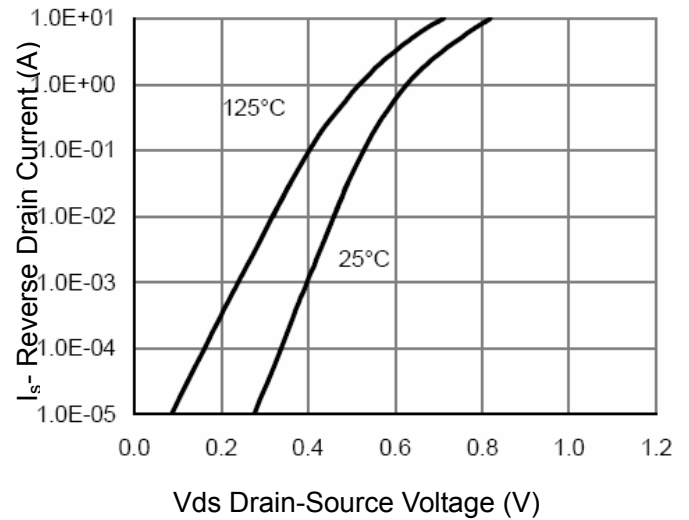
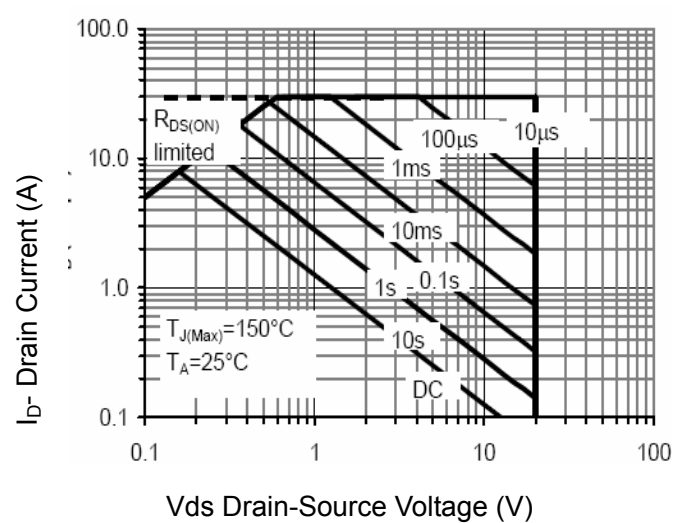
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 10	μA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=8A$	-	11	13	m Ω
		$V_{GS}=2.5V, I_D=6.5A$	-	12.8	17	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	-	15	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	1800	-	PF
Output Capacitance	C_{oss}		-	230	-	PF
Reverse Transfer Capacitance	C_{rss}		-	200	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1.2\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	2.5		nS
Turn-on Rise Time	t_r		-	7.2		nS
Turn-Off Delay Time	$t_{d(off)}$		-	49		nS
Turn-Off Fall Time	t_f		-	10.8		nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=8A,$ $V_{GS}=4.5V$	-	17.9		nC
Gate-Source Charge	Q_{gs}		-	1.5	-	nC
Gate-Drain Charge	Q_{gd}		-	4.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V_{SD}	$V_{GS}=0V, I_S=8A$	-	-	1.2	V
Diode Forward Current <small>(Note 2)</small>	I_S		-	-	8	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

Figure 1: Switching Test Circuit

Figure 2: Switching Waveforms

Figure 3 Power Dissipation

Figure 6 Drain-Source On-Resistance

Figure 5 Output Characteristics

Figure 8 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 9 $R_{DS(on)}$ vs V_{GS}

Figure 11 Gate Charge

Figure 8 Capacitance vs V_{DS}

Figure 10 Source-Drain Diode Forward

Figure 13 Safe Operation Area

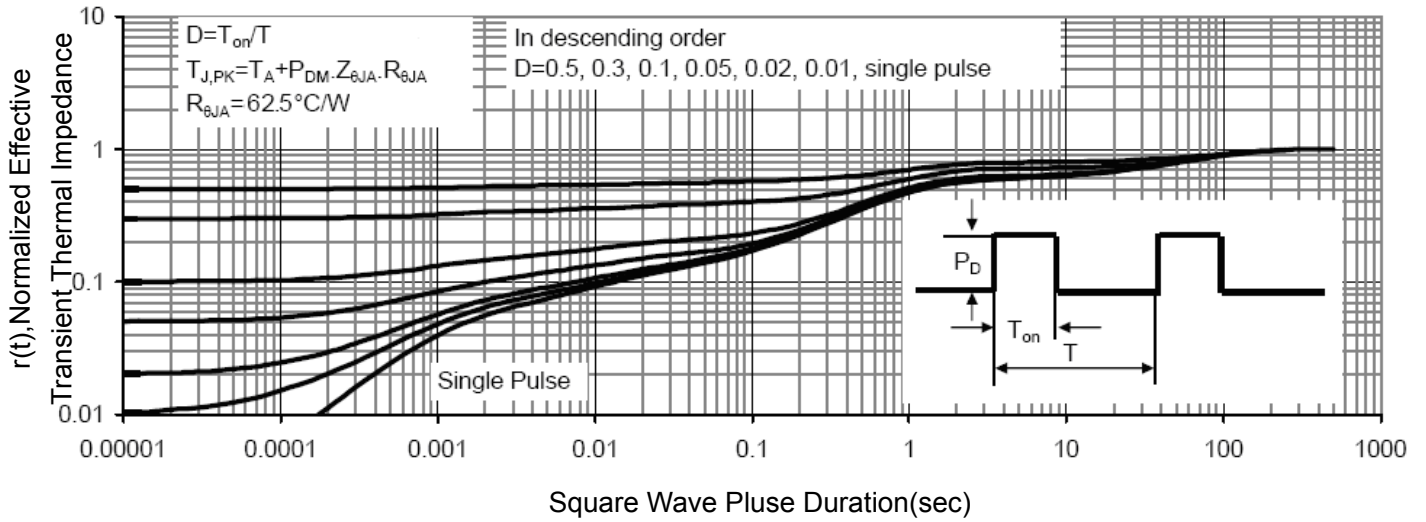
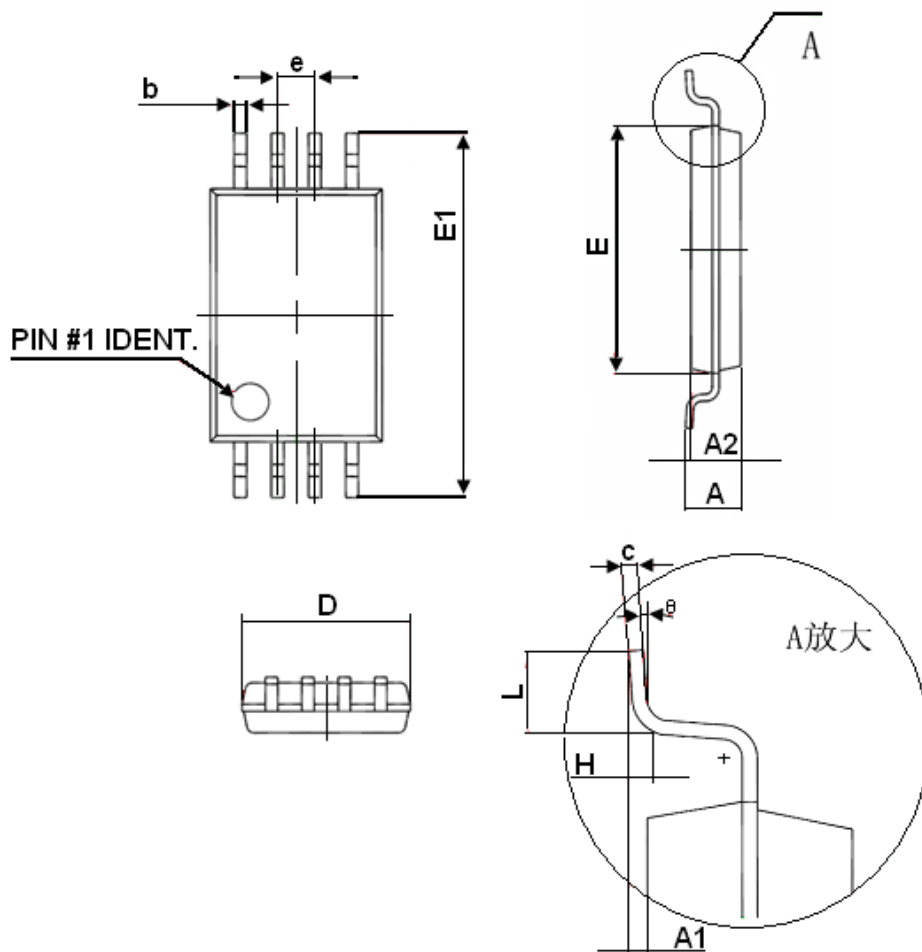


Figure 14 Normalized Maximum Transient Thermal Impedance

Tssop-8 Package Information


Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.100
A2	0.800	1.000
A1	0.020	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
θ	1°	7°

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- FNK will supply the best possible product for customers!